Surface Mount Schottky Power Rectifier

SMA Power Surface Mount Package

This device employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity diodes in surface mount applications where compact size and weight are critical to the system.

Features

- Small Compact Surface Mountable Package with J-Bent Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop
- Guardring for Stress Protection
- This is a Pb-Free Device

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 70 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped in 12 mm tape, 5000 units per 13 inch reel
- Polarity: Cathode Lead Indicated by Either Notch in Plastic Body or Polarity Band

1



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SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES 40 VOLTS



SMA CASE 403D PLASTIC





A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
NRVBA140T3G	SMA (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating		Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	40	٧
Average Rectified Forward Current (At Rated V_R , $T_C = 95^{\circ}C$)	Io	1.0	Α
Peak Repetitive Forward Current (At Rated V _R , Square Wave, 20 kHz, T _C = 100°C)	I _{FRM}	2.0	Α
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	30	Α
Storage Temperature	T _{stg}	-55 to +150	°C
Operating Junction Temperature	TJ	-55 to +125	°C
Voltage Rate of Change (Rated V_R , $T_J = 25$ °C)	dv/dt	10,000	V/μs
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

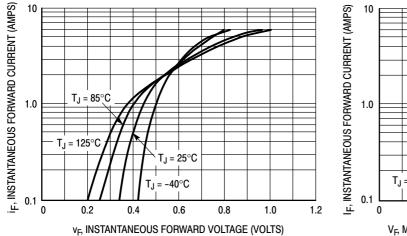
THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Note 1)	$R_{ heta JL}$	35	°C/W
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	86	

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 2)		V _F	T _J = 25°C	T _J = 100°C	V
see Figure 2 for other Values	(I _F = 1.0 A) (I _F = 2.0 A)		0.55 0.71	0.505 0.74	
Maximum Instantaneous Reverse Current		I _R	T _J = 25°C	T _J = 100°C	mA
see Figure 4 for other Values	(V _R = 40 V) (V _R = 20 V)		0.5 0.1	10 4.0	

Mounted on 2" Square PC Board with 1" Square Total Pad Size, PC Board FR4.
Pulse Test: Pulse Width ≤ 250 μs, Duty Cycle ≤ 2.0%.



1.0 T_J = 85°C T_J = 25°C T_J = 25°C T_J = 25°C V_E MAXIMUM INSTANTANEOUS FORWARD VOLTAGE (VOLTS)

Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

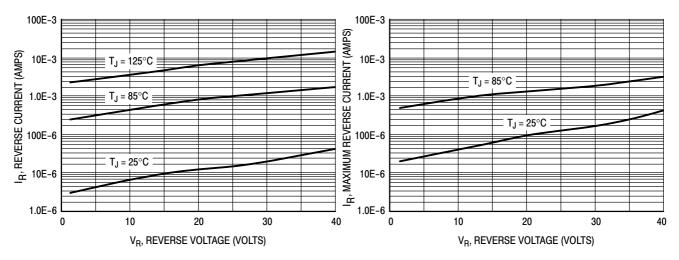
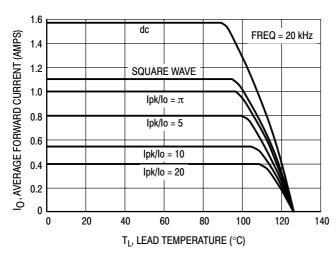


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current



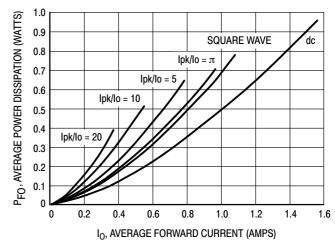


Figure 5. Current Derating

Figure 6. Forward Power Dissipation

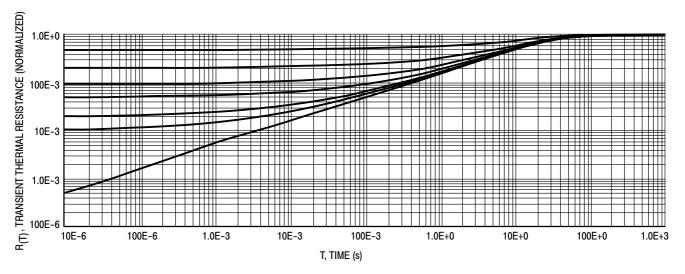


Figure 7. Thermal Response

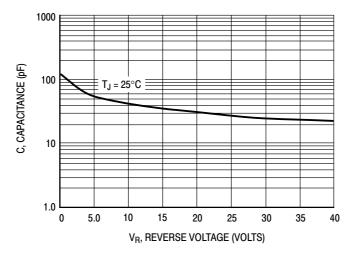


Figure 8. Capacitance

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